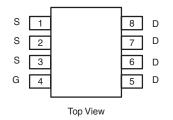


Vishay Siliconix

P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	V _{DS} (V) R _{DS(on)} (Ω)				
	0.0075 at V _{GS} = - 4.5 V	- 14			
- 20	0.009 at V _{GS} = - 2.5 V	- 13			
	0.0115 at V _{GS} = - 1.8 V	- 12			



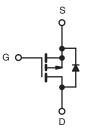


FEATURES

- Halogen-free According to IEC 61249-2-21
 Definition
- TrenchFET[®] Power MOSFET
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

- Game Station
 - Load Switch



P-Channel MOSFET

Ordering Information:	Si4423DY-T1-E3 (Lead (Pb)-free)
	Si4423DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25 \text{ °C}$, unless otherwise noted					
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 20		V
Gate-Source Voltage		V _{GS}	± 8		v
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	I _D	- 14	- 10	•
	T _A = 70 °C		- 11.5	- 8	
Pulsed Drain Current		I _{DM}	- 50		А
Continuous Source Current (Diode Conduction) ^a		۱ _S	- 2.7	- 1.36	
	T _A = 25 °C	P _D	3.0	1.5	w
Maximum Power Dissipation ^a	T _A = 70 °C		1.9	0.95	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 t	o 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	t ≤ 10 s	R _{thJA}	33	42	
Maximum Junction-to-Ambient	Steady State		70	84	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	16	21	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.



COMPLIANT

HALOGEN

Available

Vishay Siliconix



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static				•		
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -600 \ \mu A$	- 0.4		- 0.9	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 8 V$			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -20 V, V_{GS} = 0 V$			- 1	μΑ
		V_{DS} = - 20 V, V_{GS} = 0 V, T_{J} = 70 °C			- 10	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = -5 V, V_{GS} = -4.5 V$	- 30			Α
		V _{GS} = - 4.5 V, I _D = - 14 A		0.006	0.0075	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V_{GS} = - 2.5 V, I_D = - 13 A		0.0071	0.009	Ω
		V_{GS} = - 1.8 V, I _D = - 12 A		0.009	0.0115	
Forward Transconductance ^a	g _{fs}	V _{DS} = - 10 V, I _D = - 14 A		60		S
Diode Forward Voltage ^a	V_{SD}	$I_{S} = -2.7 \text{ A}, V_{GS} = 0 \text{ V}$		- 0.6	- 1.1	V
Dynamic ^b						
Total Gate Charge	Qg			116	175	
Gate-Source Charge	Q _{gs}	V_{DS} = - 10 V, V_{GS} = - 5 V, I_D = - 14 A		16		nC
Gate-Drain Charge	Q _{gd}			27		
Gate Resistance	R _g			3.2		Ω
Turn-On Delay Time	t _{d(on)}			75	115	
Rise Time	t _r	V_{DD} = - 10 V, R_L = 10 Ω		165	250	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 1 A, V_{GEN} = - 4.5 V, R_g = 6 Ω		460	700	ns
Fall Time	t _f			210	320	110
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 2.1 A, dl/dt = 100 A/µs		105	160	

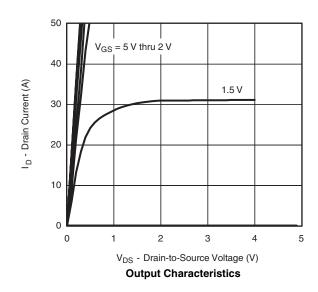
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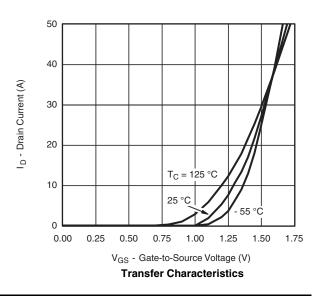
a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

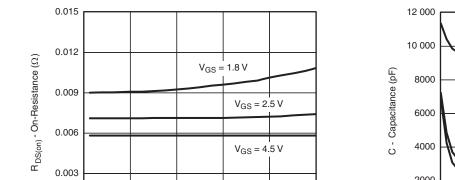
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





Si4423DY

Vishay Siliconix



24

I_D - Drain Current (A)

32

40

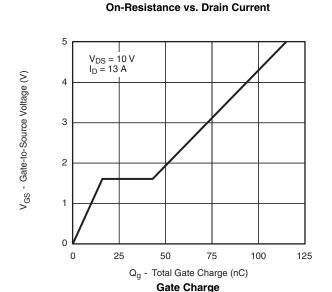
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

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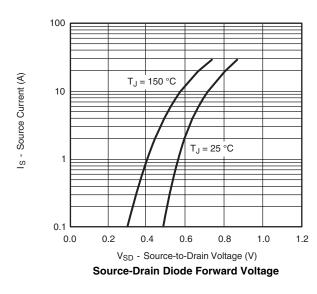
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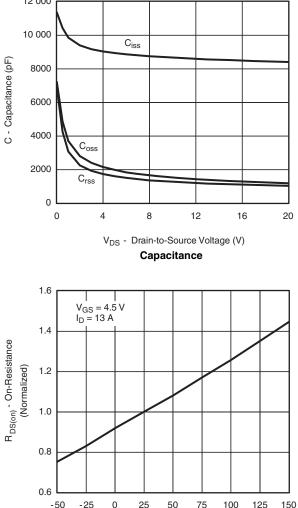
0

8



16





T_J - Junction Temperature (°C) **On-Resistance vs. Junction Temperature**

50

75

100

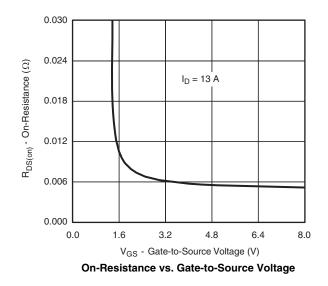
125

150

- 50

0

25

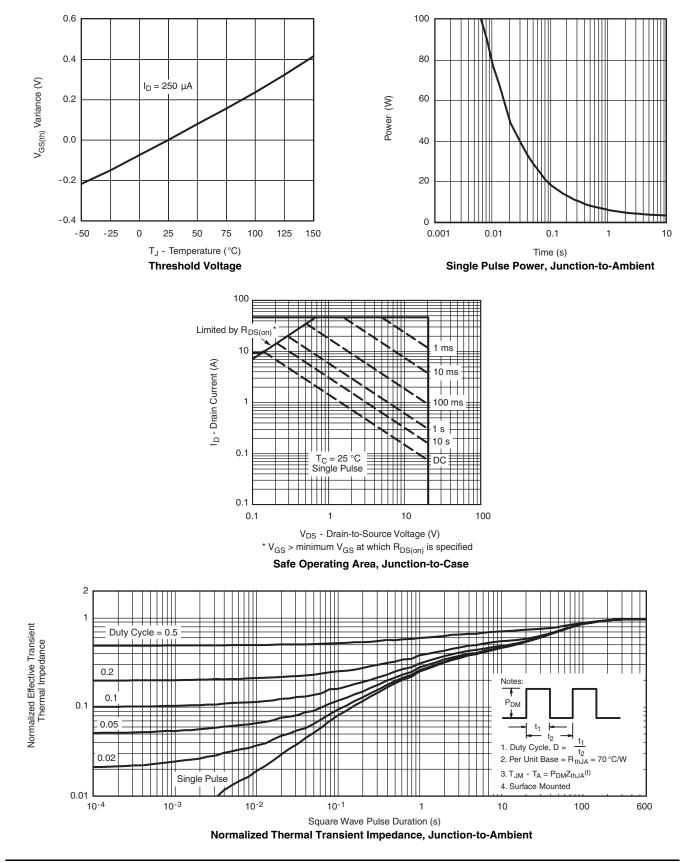


Document Number: 72085 S09-0705-Rev. D, 27-Apr-09

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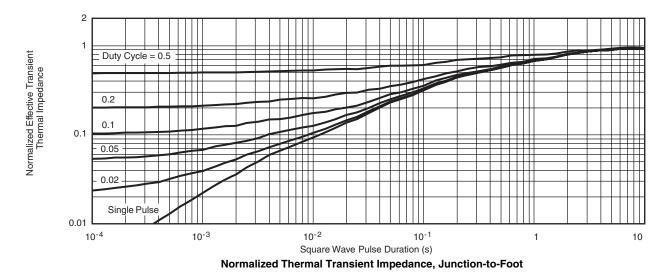
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





Si4423DY Vishay Siliconix

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72085.

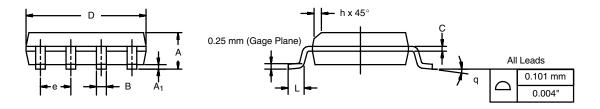


Package Information

Vishay Siliconix

SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012





	MILLIM	IETERS	INC	HES		
DIM	Min	Мах	Min	Max		
A	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
E	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050 BSC			
н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498						

Application Note 826

Vishay Siliconix



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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